IRFP27N60K, SiHFP27N60K

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THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R _{thJA}	-	40	
Case-to-Sink, Flat, Greased Surface	R _{thCS}	0.24	-	°C/W
Maximum Junction-to-Case (Drain)	R _{thJC}	-	0.29	

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static		•					
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0 V, I _D = 250 μA	600	-	-	V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	Referen	ce to 25 °C, I _D = 1 mA	-	640	-	mV/°C
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS}	$= V_{GS}, I_D = 250 \mu A$	3.0	-	5.0	V
Gate-Source Leakage	I _{GSS}		$V_{GS} = \pm 30 \text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current		V _{DS} :	$V_{DS} = 600 \text{ V}, V_{GS} = 0 \text{ V}$		-	50	
Zero date voltage Brain ourient	I _{DSS}	$V_{DS} = 480^{\circ}$	V, V _{GS} = 0 V, T _J = 125 °C	-	-	250	μA
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 16 A ^b	-	0.18	0.22	Ω
Forward Transconductance	9 _{fs}	V_{DS}	$= 50 \text{ V}, I_D = 16 \text{ A}$	14	-	-	S
Dynamic							
Input Capacitance	C_{iss}		$V_{GS} = 0 V$	-	4660	-	
Output Capacitance	C _{oss}		V _{DS} = 25 V		460	-	- pF
Reverse Transfer Capacitance	C_{rss}	f = 1.0 MHz, see fig. 5		-	41	-	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 1.0 V , f = 1.0 MHz	-	5490	-	pi
		$V_{GS} = 0 V$	$V_{DS} = 480 \text{ V}$, $f = 1.0 \text{ MHz}$	-	120	-	
Effective Output Capacitance	C _{oss} eff.	$V_{GS} = 0 V$	V _{DS} = 0 V to 480 V	-	250	-	
Total Gate Charge	Q_g		1 07 A V 400 V	-	-	180	
Gate-Source Charge	Q _{gs}	$V_{GS} = 10 \text{ V}$ $I_D = 27 \text{ A}, V_{DS} = 480 \text{ V}$	-	-	56	nC	
Gate-Drain Charge	Q_{gd}	see fig. 6 and 13 ^b		-	-		86
Turn-On Delay Time	t _{d(on)}			-	27	-	
Rise Time	t _r	V _{DD} = 300 V, I _D = 27 A		-	110	-	1
Turn-Off Delay Time	t _{d(off)}	$R_0 = 4.3 \Omega$, V _{GS} = 10 V, see fig. 10 ^b	-	43	-	ns -
Fall Time	t _f	9	, 45	-	38	-	
Drain-Source Body Diode Characteristic	cs						
Continuous Source-Drain Diode Current	Is	MOSFET sym showing the	MOSFET symbol showing the		-	27	- A
Pulsed Diode Forward Current ^a	I _{SM}	integral reverse p - n junction diode		-	-	110	
Body Diode Voltage	V_{SD}	$T_{J} = 25 ^{\circ}\text{C}, I_{S} = 27 \text{A}, V_{GS} = 0 \text{V}^{\text{b}}$		-	-	1.5	V
Body Diode Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = 27 A, dl/dt = 100 A/μs ^b		-	620	920	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	11	16	μC
Reverse Recovery Current	I _{RRM}			-	36	53	Α
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)		1 \			

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300~\mu s;$ duty cycle $\leq 2~\%.$
- c. C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80% V_{DS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

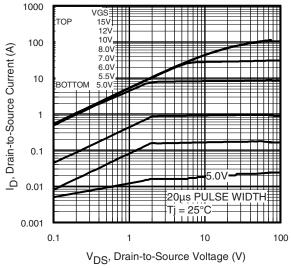


Fig. 1 - Typical Output Characteristics

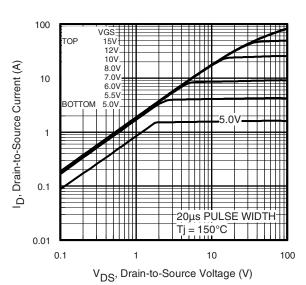


Fig. 2 - Typical Output Characteristics

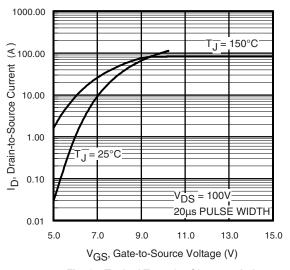


Fig. 3 - Typical Transfer Characteristics

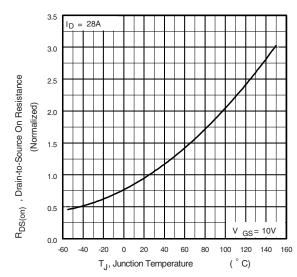


Fig. 4 - Normalized On-Resistance vs. Temperature

IRFP27N60K, SiHFP27N60K

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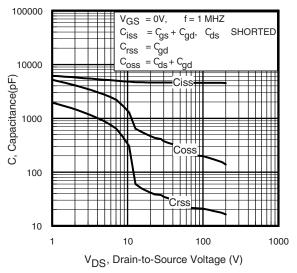


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

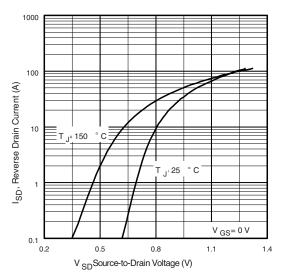


Fig. 7 - Typical Source-Drain Diode Forward Voltage

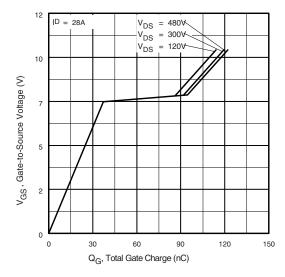


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

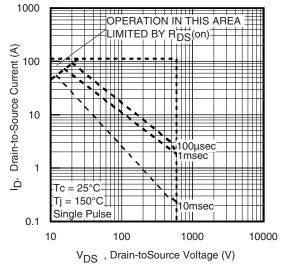


Fig. 8 - Maximum Safe Operating Area

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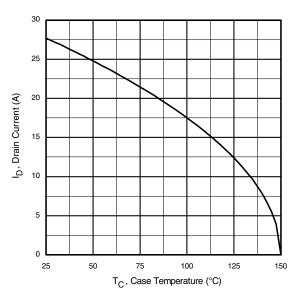


Fig. 9 - Maximum Drain Current vs. Case Temperature

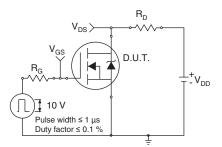


Fig. 10a - Switching Time Test Circuit

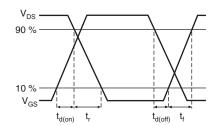


Fig. 10b - Switching Time Waveforms

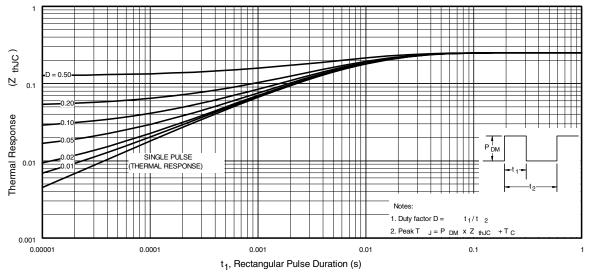


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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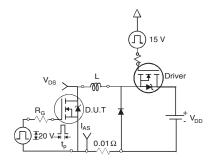


Fig. 12a - Unclamped Inductive Test Circuit

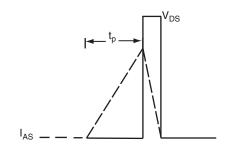


Fig. 12b - Unclamped Inductive Waveforms

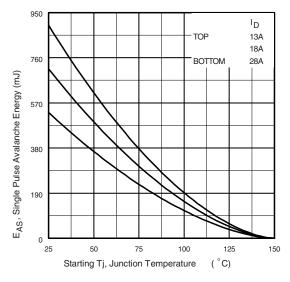


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

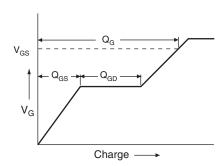


Fig. 13a - Basic Gate Charge Waveform

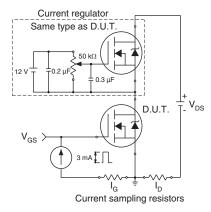
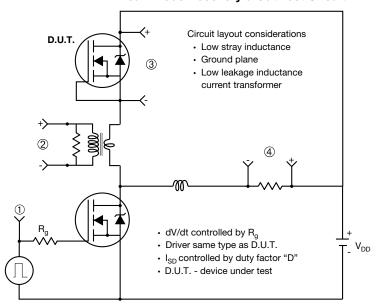


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



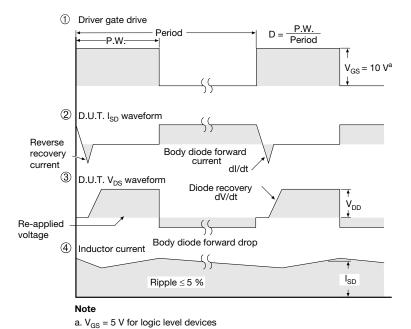


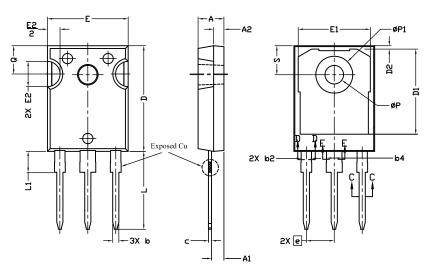
Fig. 14 - For N-Channel

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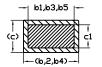


TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9







Section C--C,D--D,E--E

	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
Α	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44 BSC		
L	14.90	15.40	
L1	3.96	4.16	6
ØΡ	3.56	3.65	7
Ø P1	7.19 ref.		
Q	5.31	5.69	
S	5.54	5.74	

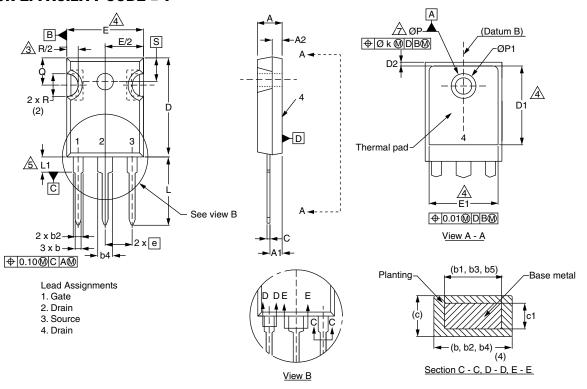
Notes

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- $^{(7)}$ Ø P to have a maximum draft angle of 1.5 $^\circ$ to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

Revision: 19-Oct-2020 1 Document Number: 91360

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VERSION 2: FACILITY CODE = Y



	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	5.46 BSC	
Øk	0.254		
L	14.20	16.25	
L1	3.71	4.29	
ØΡ	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

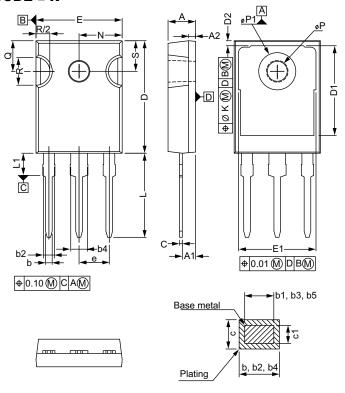
Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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VERSION 3: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	4.65	5.31	
A1	2.21	2.59	
A2	1.17	1.37	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.65	2.39	
b3	1.65	2.34	
b4	2.59	3.43	
b5	2.59	3.38	
С	0.38	0.89	
c1	0.38	0.84	
D	19.71	20.70	
D1	13.08	-	

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46 BSC		
k	0.254		
L	14.20	16.10	
L1	3.71	4.29	
N	7.62 BSC		
Р	3.56	3.66	
P1	=	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

ECN: E20-0545-Rev. F, 19-Oct-2020

DWG: 5971

Notes

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

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